Charge transfer dynamics in MoSe$_2$/hBN/WSe$_2$ heterostructures

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Abstract

Ultrafast charge transfer processes provide a facile way to create interlayer excitons\textsuperscript{1-3} and to generate single-cycle THz pulses\textsuperscript{4} in directly contacted transition metal dichalcogenide (TMD) layers. More sophisticated heterostructures composed of TMD/hBN/TMD can enable new ways to control the charge transfer dynamics to achieve novel exciton phenomena, such as exciton insulators\textsuperscript{5-7} and exciton condensates\textsuperscript{8}, where longer lifetimes are desired. In this work, we experimentally study charge transfer dynamics in a heterostructure composed of a 1-nm-thick hBN spacer between MoSe\textsubscript{2} and WSe\textsubscript{2} monolayers. We observe the interlayer charge transfer from MoSe\textsubscript{2} to WSe\textsubscript{2} across hBN with a time constant of 500 ps, which is over three orders of magnitude slower compared to the charge transfer between TMD layers without an hBN spacer. Furthermore, we observe strong competition between the interlayer charge transfer process with the intralayer exciton-exciton annihilation process at high excitation densities. Our work opens possibilities to understand charge transfer pathways in TMD/hBN/TMD heterostructures for the efficient generation and control of interlayer excitons.
Interlayer excitons are bound electron-hole pairs where the constituent electron and hole are spatially separated near the junction of two layered semiconductors. They are energetically favorable in a heterobilayer with type-II band alignment or in a homobilayer with an out-of-plane electric field. In directly contacted transition metal dichalcogenide (TMD) heterostructures, interlayer excitons can be easily generated by any optical excitations above one of the intralayer exciton energies, owing to ultrafast and efficient charge transfer processes from one layer to the other.\textsuperscript{1-3}

Adding a thin hexagonal boron nitride (hBN) layer to make a TMD/hBN/TMD heterostructure provides the opportunity to engineer many properties of the interlayer excitons, ranging from their binding energy, the dipolar exciton-exciton interaction strength, and the charge transfer dynamics. Since electrons reside in one layer and holes reside in the other layer that are separated by the hBN layer, the spatial overlap between their wavefunctions is poor and their radiative lifetimes can be much longer\textsuperscript{6} than those of directly contacted TMD/TMD heterostructures.\textsuperscript{9,10} Long lifetime is one of the key properties that allow us to reach novel excitonic phases including excitonic insulators\textsuperscript{5-7} and Bose-Einstein condensates, where they need to interact for a sufficiently long time before they recombine and disappear. In addition, the aligned nature of the permanent dipole moments of interlayer excitons leads to enhanced exciton-exciton interaction strength with increased hBN thickness.\textsuperscript{11} The dipolar interaction strength of interlayer excitons can exceed the exchange interaction between neutral excitons, which can be used to stabilize the strongly correlated excitonic phases.\textsuperscript{6,12,13}

Although the hBN layer is beneficial for realizing long-lived and strongly correlated interlayer excitons, it exponentially suppresses the tunneling probability and the charge transfer rate. This will hamper the generation of such interlayer excitons through optical excitations. An experimental study of these effects in TMD/hBN/TMD heterostructures would be crucial for understanding the dynamics of interlayer exciton formation and for optimizing the strongly correlated excitonic phases.

Transient absorption spectroscopy is a powerful tool to investigate the interlayer exciton dynamics, where pump-induced changes of absorption peaks are probed as a function of the time delay between pump and probe pulses. Since the intralayer exciton peak changes (induced by the presence of interlayer excitons) are probed in these measurements, the vanishing oscillator strength of interlayer excitons\textsuperscript{10} does not prohibit the measurement; for this reason, transient absorption
spectroscopy has been primarily used to study the dynamics of charge transfer processes\textsuperscript{1–3,14–16}. Here, using the same technique, we investigate the ultrafast charge transfer dynamics in a heterostructure composed of a 1-nm-thick hBN spacer between MoSe\textsubscript{2} and WSe\textsubscript{2} monolayers. We reveal that the hole transfer from MoSe\textsubscript{2} to WSe\textsubscript{2} across hBN takes place with a time constant of \( \sim 500 \) ps, which is over three orders of magnitude slower compared to the charge transfer between directly contacted TMD layers (<100 fs). In addition, we show that there is a strong competition between the interlayer charge transfer and the intralayer exciton-exciton annihilation processes in this system at high excitation densities.

Figures 1a and 1b illustrate our experimental scheme. We first create MoSe\textsubscript{2} intralayer excitons using a resonant pump pulse, which essentially does not create WSe\textsubscript{2} excitons (\( E_{\text{pump}} \approx E_{\text{MoSe}_2} < E_{\text{WSe}_2} \)). After a time delay (\( \Delta t = t_{\text{probe}} - t_{\text{pump}} \)), a broadband probe pulse (1.55-1.91 eV) measures the WSe\textsubscript{2} intralayer exciton absorption peak. Holes dissociated from the MoSe\textsubscript{2} excitons are transferred to the WSe\textsubscript{2} layer and relaxed to its band edge, which saturate the WSe\textsubscript{2} intralayer exciton absorption by Pauli blocking. A microscope image and schematic layered structure are shown in Figs. 1c and 1d (the layer dimensions are in Table S1). The spacer hBN consists of three atomic layers, which is confirmed by an atomic force microscope (AFM) measurement (see Fig. S1). The twist angle between MoSe\textsubscript{2} and WSe\textsubscript{2} layers is determined to be 19.5° using a polarization-dependent second-harmonic generation measurement (see Fig. S2).

Due to limitations in typical experimental configurations (e.g., opaque substrate or cryostat sample holder), it is common that only the reflection is measured. To separate the optical features of the sample (MoSe\textsubscript{2}/hBN/WSe\textsubscript{2}) from the background (substrate and other dielectric layers) and to eliminate the effect of an uneven spectrum of the incident light, we measure a reflection contrast spectrum, defined as \( (I_{r}^{sb} - I_{r}^{b})/I_{r}^{b} \), where \( I_{r}^{sb} \) is a reflection spectrum measured in a region with sample and background (“sb”), and \( I_{r}^{b} \) is a reflection spectrum measured in a background (“b”) region, as defined in Fig. 1d. The measured reflection contrast and pump spectra are shown in Fig. 1e. The pump is mostly resonant with MoSe\textsubscript{2} excitons, although it is slightly redshifted to reduce the direct effect on the WSe\textsubscript{2} layer. The small mismatch is taken into account in the calibration of pump absorption by the MoSe\textsubscript{2} layer (see Fig. S5).

The local field at the TMD layers can be vastly different from that of a free-space field due to the interference between reflections from multiple interfaces in a layered structure. Depending on the structural dimensions and dielectric properties of the substrate, the Fano-like lineshapes and
peak heights of resonances can vary dramatically even with an identical TMD layer. Therefore, it is crucial to perform transfer-matrix calculations to estimate the absolute values of absorption (see Supplemental Information for details of the calibration). A result of the transfer-matrix fitting to the measured reflection contrast spectrum, starting from known thicknesses and dielectric constants of each layer, is shown as the orange line in Fig. 1e. From the absolute values of the reflection contrast spectrum, not only the central energies and linewidths are extracted, but also the absolute values of absorption by each TMD layer are determined (see Fig. S5), which cannot be simply read from the reflection contrast values.

Figure 2a shows representative transient reflection spectra measured by the probe with and without the pump, which we denote as $R_{\text{pump on}}$ and $R_{\text{pump off}}$, respectively. The pump-on spectrum is taken at a pump-probe time delay when the hole transfer is completed ($\Delta t = 60$ ps). A probe spectrum in the background region is also measured to obtain the reflection contrast spectra shown in Fig. 2b. At this high pump fluence ($F_{\text{pump}} = 39.4 \mu J/cm^2$), the exciton absorption peak saturates and the trion absorption peak ($\sim 20$ meV below the exciton energy) emerges. Transfer-matrix calculations including these two peaks can successfully reproduce the measured reflection contrast spectra shown in Fig. 2b, and the extracted absorption profiles are shown in Fig. 2c.

We then varied the time delay to measure the charge transfer dynamics. Figures 3a and 3b show the transient reflection spectra at low and high pump fluences, respectively. To visualize small changes in the reflection intensities, we plotted their differential changes, namely, $\Delta R/R = (R_{\text{pump on}} - R_{\text{pump off}})/R_{\text{pump off}}$. In stark contrast with that measured in similar devices without any hBN spacer\(^1\), Fig. 3a shows that the WSe\(_2\) exciton peak at 1.6923 eV rises slowly and saturates by $\sim 100$ ps when the pump fluence is low, which corresponds to the initial MoSe\(_2\) exciton density of $n_m(\Delta t = 0) = 4.6 \times 10^{11}$ cm\(^{-2}\). When the initial MoSe\(_2\) exciton density is increased to $n_m(0) = 2.7 \times 10^{12}$ cm\(^{-2}\), the WSe\(_2\) exciton peak saturates by $\sim 20$ ps, as shown in Fig. 3b. The observed density-dependent dynamics suggests that nonlinear interactions are involved in the charge transfer process in the MoSe\(_2\)/hBN/WSe\(_2\) heterostructure. The vertical line cuts of transient reflection spectra at various time delays are shown in Figs. 3c and 3d, which reveal both the saturation of the exciton peak and the appearance of a trion peak.

To quantitatively measure physical properties, we analyzed the reflection contrast spectrum at each time delay and fit using the transfer-matrix calculation. We used the Lorentzian oscillator model with complex dielectric constants to approximate the WSe\(_2\) absorption resonance and used
the oscillator strength $f$, central energy $E$, and linewidth $\Gamma$ as fitting parameters at each time delay. Other parameters are fixed to the values obtained from the fitting without the pump (the fit result shown in Fig. 1e). The time traces of the extracted quantities are plotted in Fig. 4. We calculated $\Delta A/A = (A_{\text{pump on}} - A_{\text{pump off}})/A_{\text{pump off}}$, where $A$ is the absolute value of the absorption, as well as the pump-induced linewidth broadening $\Delta \Gamma = \Gamma_{\text{pump on}} - \Gamma_{\text{pump off}}$ and pump-induced energy shift $\Delta E = E_{\text{pump on}} - E_{\text{pump off}}$. An excitation-density-dependent saturation dynamics is observed (Fig. 4a) and the linewidth broadening dynamics follows a similar trend (Fig. 4b). The absorption saturation and linewidth broadening effects can be understood as a result of the Pauli blocking at the WSe$_2$ exciton state by the transferred holes. On the other hand, the peak energy slightly redshifts immediately at $\Delta t = 0$ and then blueshifts at later time delays. We attribute this behavior to the dielectric screening effect from all carriers, including those directly excited in the MoSe$_2$ layer. Therefore, the effect occurs instantaneously after the optical excitation and does not reflect the charge transfer dynamics. After the carrier-induced screening decays, the transferred holes result in the blueshift of the WSe$_2$ exciton peak, as described by repulsive polarons. We emphasize that such spectral analysis and transfer-matrix calculations are crucial to obtain meaningful results from transient reflection data.

From a separate gate-dependent reflection contrast measurement (see Fig. S6), we were able to correlate the density of transferred holes in the WSe$_2$ layer, $n_w$, and the change of WSe$_2$ exciton absorption induced by hole doping. This way, we can convert the $\Delta A/A$ data (as in Fig. 4a) to $n_w$, which is plotted in Fig. 5a as a function of the time delay and excitation density. The estimated density of MoSe$_2$ excitons created by the pump, $n_m(\Delta t = 0)$, ranges from $5.6 \times 10^{10}$ cm$^{-2}$ to $5.5 \times 10^{12}$ cm$^{-2}$ (see Supplemental Information for details of the calibration). The hole transfer timescale is not only much slower than that without a spacer hBN but also strongly density dependent. Due to the slower timescale, it competes with several other processes at the picosecond timescale. Most importantly, the exciton-exciton annihilation process within the MoSe$_2$ layer becomes very important at higher pump fluences$^{17,18}$.

The maximum density of transferred holes, $\max[n_w(\Delta t)]$, is plotted in Fig. 5b and the charge transfer efficiency, defined as $\max[n_w(\Delta t)]/n_m(0)$, is plotted in Fig. 5c. As the excitation density is increased, there is increased competition between the charge transfer and other nonlinear processes, which leads to a less efficient transfer. This behavior is different from devices without an hBN spacer, where the charge transfer process dominates all other losses and a linear increase
of \( \max[n_w(\Delta t)] \) is observed as a function of \( n_m(0) \). In a similar device but with a 3-nm-thick hBN spacer, the charge transfer becomes too slow and inefficient, so we were not able to measure any appreciable change of the WSe\(_2\) exciton peak within the measurement window (500 ps).

To quantitatively understand the density-dependent dynamics and competition between different processes, we used coupled rate equations to solve for the transferred hole population. The exciton density in the MoSe\(_2\) layer is denoted by \( n_m \), while the density of transferred holes in the WSe\(_2\) layer is denoted by \( n_w \). The rates of their population change can be expressed as

\[
\frac{dn_m}{dt} = -\gamma_m n_m - \frac{1}{2} \gamma_{mm} n_m^2 - \gamma_t n_m \\
\frac{dn_w}{dt} = -\gamma_w n_w + \gamma_t n_m + \frac{1}{2} \alpha \gamma_{mm} n_m^2
\]

where \( \gamma_m \) is the MoSe\(_2\) exciton population decay rate, \( \gamma_w \) is the WSe\(_2\) hole population decay rate, \( \gamma_{mm} \) is the MoSe\(_2\) exciton-exciton annihilation rate, and \( \gamma_t \) is the hole transfer rate from MoSe\(_2\) to WSe\(_2\). The last term in Eq. (2) represents a nonlinear charge transfer mechanism, where the high-energy excitations created by the exciton-exciton annihilation provide additional transfer pathways.

We numerically solved the coupled differential equations with fitting parameters to reproduce the measured density-dependent dynamics and plotted them in Fig. 5a as gray dotted lines. The global parameters that give best fits to all excitation densities are \( \gamma_m = (100 \text{ ps})^{-1} \), \( \gamma_w = (4 \text{ ns})^{-1} \), \( \gamma_{mm} = 0.3 \text{ cm}^2/\text{s} \), and \( \gamma_t = (500 \text{ ps})^{-1} \) (see Fig. S7 for fit results using different starting parameters). The value of \( \gamma_{mm} \) is consistent with that observed in a previous study with a MoSe\(_2\) monolayer\(^{18}\) and the intralayer exciton decay rate \( \gamma_m \) represents the effective rate that includes radiative decay, nonradiative decay, and the dynamics between bright and dark excitonic species\(^{19}\). Note that, without the nonlinear charge transfer term \( \frac{1}{2} \alpha \gamma_{mm} n_m^2 \), the very steep saturation at higher excitation densities cannot be reproduced with any reasonable fit parameter values. We estimate that \( \alpha = 0.023 \), which implies that about 2.3% of the annihilated particles eventually find a way to the WSe\(_2\) layer.

The hole transfer time of 500 ps is over three orders of magnitude longer than that observed in a directly contacted MoSe\(_2\)/WSe\(_2\) heterostructure (<100 fs). The phonon relaxation time to the band edge is negligibly short (optical phonons at 40 meV can be efficiently emitted at the femtosecond timescale\(^{20,21}\)), so the charge transfer process is only slowed down by the increased
tunneling barrier and reduced interlayer coupling. However, even though the transfer timescale is much slower, the overall transfer efficiency is still significant.

The measured efficiency shown in Fig. 5c gives additional bounds to the fitting result. In the low excitation-density limit, the analytical solutions of Eqs. (1) and (2) show that the transfer efficiency should be \( \gamma_t / (\gamma_t + \gamma_m) \). The measured efficiency of 16% at the lowest excitation density implies that the transfer time \( \tau_t \) is about five times longer than the exciton lifetime \( \tau_m \), which is consistent with the fit results. In addition, we exclude the possibility of faster charge transfer at higher excitation densities, which would result in higher transfer efficiencies at higher excitation densities. Therefore, we confirm that the measured transfer rate is indeed hundreds of picoseconds.

In conclusion, we used a thin hBN spacer between MoSe\(_2\) and WSe\(_2\) monolayers to study the effects of the tunneling barrier on the charge transfer timescale and efficiency. We extracted pump-induced saturation, energy shift, and linewidth broadening at each time delay to distinguish different processes that affect the absorption peak. Density-dependent saturation dynamics reveal competing processes such as exciton-exciton annihilation and nonlinear charge transfer processes. By fitting the solution of coupled rate equations to the measured density-dependent charge transfer dynamics, we found that the intrinsic charge transfer time is \( \sim 500 \) ps, which is over three orders of magnitude slower than that without the spacer. Our work opens possibilities of investigating the factors contributing to charge transfer, e.g., the effects of momentum mismatch between the layers, which have not been feasible in directly contacted TMD heterostructures due to the extremely fast timescale. Understanding the charge transfer process across various thicknesses of an hBN spacer will allow us to further optimize the generation and control of interlayer excitons with tunable dipole moment and lifetime.

**Methods**

**Device fabrication and characterization**
The hBN-encapsulated MoSe\(_2\)/hBN/WSe\(_2\) heterostructure was fabricated using a dry transfer technique based on polypropylene carbonate (PPC\(^{22} \). The exfoliated MoSe\(_2\) and WSe\(_2\) monolayers are separated by a thin hBN layer with a thickness of around 1 nm. Two additional few-layer graphite (FLG) are in contact with the MoSe\(_2\) and WSe\(_2\) monolayers, respectively, and encapsulated by bottom and top hBN layers. The bottom and top gates are also made of FLG. The stack is finally released on a 285 nm SiO\(_2\)/Si substrate. A standard photolithography system
(Durham Magneto Optics, MicroWriter) is used to define the electrodes, and an e-beam deposition system is used for the 5 nm Cr/100 nm Au deposition. The WSe$_2$ monolayer, MoSe$_2$ monolayer, top and bottom gates, and heavily hole-doped Si are grounded during the measurements unless otherwise noted.

**Pump-probe spectroscopy**

Yb-based femtosecond laser (Light Conversion CARBIDE, wavelength $\lambda = 1030$ nm, repetition rate $f_{\text{rep}} = 151.3$ kHz) was used as a “fundamental” beam for an optical parametric amplifier (OPA, Light Conversion ORPHEUS). The OPA signal energy was tuned to be resonant with the MoSe$_2$ exciton energy ($E_{\text{pump}} = 1.6165$ eV, $\lambda_{\text{pump}} = 767$ nm) and used as a “pump” beam. The leftover fundamental beam was focused onto a 3-mm-thick sapphire crystal to generate a supercontinuum, which was filtered to let through $E_{\text{probe}} = 1.55$-1.91 eV and used as a “probe” beam. The pulse durations (full width at half maximum, FWHM, of the intensity envelope) of both pump and probe pulses were initially 200 fs but elongated to 250 fs after passing through multiple optical components including an objective lens (20×, NA 0.45). The FWHM of the pump beam’s spatial profile was 6.2 μm, while that of the probe beam was 1.6 μm (see Fig. S3). Both beams were vertically polarized except for the circular dichroism measurement. The reflected probe beam was dispersed by a transmissive grating (300 gr/mm), focused by a lens (focal length = 5 cm), and then detected by a linear camera (Coptonix, S11639-01). The pump beam was chopped at 445 Hz and the pump-probe signal $\Delta R/R$ was averaged for 3072 frames at each time delay point. Group delay dispersion induced by optical components is post-corrected during the analysis. The exact values of these parameters (pump energy, pump beam size, integration time, etc.) were varied for each measurement to optimize the signal. All measurements are done at 100 K unless otherwise noted.

**Data availability**

The data that support the findings of this study are available from the corresponding authors upon request.

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Author contributions
F.W. and Y.Y. conceived the project. Y.Y. performed pump-probe measurements and transfer-matrix calculations. Z.Z. fabricated the samples and performed the gate-dependent absorption measurement. K.W. and K.T. grew hBN crystals. S.T. grew MoSe$_2$ and WSe$_2$ crystals. All the authors discussed the results and contributed to the manuscript.

Competing interests
The authors declare no competing interests.

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Figure 1 | Charge transfer pathway and pump-probe measurement scheme. a, Charge transfer pathway in real space. A resonant pump pulse creates MoSe₂ excitons (red arrows). Holes in the MoSe₂ layer are transferred to the WSe₂ layer (blue arrow). The WSe₂ exciton peak absorption is monitored by a broadband probe pulse (yellow arrow). The transfer process is accompanied by a real-space displacement of holes by $\sim 1.6$ nm ($d_{\text{hBN}} = 1.0$ nm) and energy relaxation by $\Delta E \sim 0.3$ eV. b, Charge transfer pathway in momentum space. For the device with $\theta_{\text{twist}} = 19.5^\circ$, the transfer process is accompanied by a momentum shift of $\Delta k \sim 0.44 \text{ Å}^{-1}$. c, A microscope image of the MoSe₂/hBN/WSe₂ heterostructure. Graphite gates and contacts (gray shaded area) are grounded unless otherwise noted. d, Schematic of the layered structure. Incident pulse intensity $I_i$ is reflected ($I_r$), transmitted ($I_t$), and absorbed by the TMD layers, while only the reflected part is measured in the sample + background (“sb”) region and the background (“b”) region. e, Reflection contrast spectrum at 100 K (blue circles) and a fit (orange line) using transfer-matrix simulation described in the main text. A normalized pump spectrum is shown as the gray shaded area (inverted vertical axis on the right-hand side).
Figure 2 | Determination of WSe$_2$ absorption spectra with and without the pump. a, Raw reflection intensities of the broadband probe in the background region (yellow), sample region without the pump (blue), and sample region with the pump (orange). The pump fluence was $F_{\text{pump}} = 39.4$ μJ/cm$^2$, corresponding to the initial MoSe$_2$ exciton density $n_m(\Delta t = 0) = 3.0 \times 10^{12}$ cm$^{-2}$. The pump-on spectrum is taken at a time delay of 60 ps when the hole transfer process is completed. b, Reflection contrast spectra with and without pump (blue and orange circles, respectively). The best fits to the transfer-matrix calculations are shown as blue and orange lines. c, Extracted absorption profiles with and without pump (blue and orange lines, respectively).
Figure 3 | Pump-probe spectra and transient spectral analysis. a,b, Differential transient reflection spectra ($\Delta R/R$) as a function of the probe energy and time delay at low and high pump fluences. c,d, Line cuts of transient reflection spectra at various time delays (different colors) and at low and high pump fluences.
**Figure 4 | Transient spectral analysis as a function of time delay.** Absolute values of (a) pump-induced absorption change $\Delta A/A$, (b) pump-induced linewidth broadening $\Delta \Gamma$, and (c) pump-induced energy shift $\Delta E$, when the initial MoSe$_2$ exciton densities are $n_m(0) = 4.1 \times 10^{11}$ cm$^{-2}$ (blue) and $n_m(0) = 3.0 \times 10^{12}$ cm$^{-2}$ (orange). Circles are the best-fit parameters from the transfer-matrix calculation at each time delay, and lines are exponentially rising or decaying functions with offsets (guides to the eye).
Figure 5 | Charge transfer dynamics as a function of the initial MoSe\textsubscript{2} exciton density. a, Transferred hole density in the WSe\textsubscript{2} layer is plotted in time for different values of the initial MoSe\textsubscript{2} exciton density $n_m(\Delta t = 0)$. Black dotted lines are fit results using Eqs. (1) and (2). b, The maximum transferred hole density, $\max[n_w(\Delta t)]$, as a function of the initial MoSe\textsubscript{2} exciton density, $n_m(0)$. c, The charge transfer efficiency, defined as $\max[n_w(\Delta t)]/n_m(0)$, as a function of $n_m(0)$.
Supplemental Information for:
Charge transfer in MoSe2/hBN/WSe2 heterostructures

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1. Characterization of the hBN thickness

The spacer hBN thickness is crucial for the charge transfer dynamics and Coulomb interaction strength. We characterized the thickness using an atomic force microscope (AFM) measurement, as shown in Fig. S1. A linecut across the boundary, denoted in Fig. S1(a), is fit to a function

$$z(x) = \frac{d_{hBN}}{2} \text{erfc} \left( \frac{x - x_0}{w} \right) + ax^2 + bx + c$$  \hspace{1cm} (S1)

where $d_{hBN}$ is the hBN thickness, $\text{erfc}(x)$ is the complementary error function, $w$ is the width of the height increment at the boundary due to the finite tip radius, and $ax^2 + bx + c$ is a smooth quadratic background function. Figure S1(b) shows the raw data and Fig. S1(c) shows the result subtracted by the background. The fitted hBN thickness is 0.92 nm, which is consistent with the thickness for three atomic layers (the layer-to-layer distance of hBN crystal is 0.333 nm).

Figure S1 | Characterization of the hBN thickness. a, AFM topography of the spacer hBN. b, A background-subtracted line cut across the boundary (blue circles) and a fit result (orange line).
2. Determination of the twist angle between MoSe$_2$ and WSe$_2$ layers

The twist angle between MoSe$_2$ and WSe$_2$ layers is determined by the second-harmonic generation (SHG) method. We used femtosecond pulses at $\lambda = 800$ nm and collected the generated light intensity at $\lambda = 400$ nm, while rotating the incident linear polarization using a half waveplate. Measured polarization-dependent second-harmonic intensities in MoSe$_2$ and WSe$_2$ monolayer regions are shown in Fig. S2. From the fits, the twist angle between MoSe$_2$ and WSe$_2$ layers in the MoSe$_2$/hBN/WSe$_2$ device used in the main text is determined to be 19.5°. The second-harmonic intensity in the heterostructure region is larger than in the monolayer regions, which indicates that the twist angle is 19.5° rather than 40.5°.

![Graph showing polarization-dependent second harmonic intensities]

Figure S2 | Polarization-dependent second-harmonic intensities in the monolayer regions.

3. Pump-probe setup and beam profiles

We used a tightly focused probe beam (FWHM = 1.6 $\mu$m) and a large pump beam (FWHM = 6.2 $\mu$m) so that the beam wandering (~1 $\mu$m peak to peak) does not affect the effective pump fluence in the probed region. The large pump beam also allowed us to approximate its Gaussian profile $I(x, y) = I_0 e^{-(x^2+y^2)/2\sigma^2}$ to a flat-top profile with a corresponding area $A = 2\pi\sigma^2$. We used the following conversion to calculate pump fluence: $F_{\text{pump}} = P_{\text{pump}} / 2\pi\sigma^2 f_{\text{rep}}$, where $P_{\text{pump}}$ is the average pump power and $f_{\text{rep}}$ is the laser repetition rate. The number of incident pump photons is then calculated as $n_{\text{pump}} = F_{\text{pump}} / E_{\text{pump}}$, where $E_{\text{pump}} = 1.616$ eV is the pump-photon energy. The pump and probe beam profiles are measured with a gray-scale CMOS camera (shown in Fig.
S3). The pump-probe setup is shown in Fig. S4.

**Figure S3 | Pump and probe beam profiles.**

- **a**, An image of the pump beam on the sample and its line cuts at $x = 0$ and $y = 0$.
- **b**, A white-light image with the pump beam.
- **c**, An image of the probe beam on the sample and its line cuts at $x = 0$ and $y = 0$.
- **d**, A white-light image with the probe beam.
Figure S4 | Collinear two-color pump-probe microscopy setup. Pump (1.6165 eV) and probe (1.55-1.91 eV) beams are collinear in the excitation path. A 750-nm long-pass filter is placed in the pump path, a combination of 650-nm short-pass and 800-nm long-pass filters is placed in the probe path, and a 750-nm short-pass filter is placed in the detection path. A quarter-wave plate (QWP) is placed only in circular dichroism measurement. A half-wave plate (HWP) and polarizer (Pol) combination is used to control the pump power.

4. Absorption calibration using transfer-matrix calculation

With measured layer dimensions and known dielectric constants, we simulated the reflection contrast spectrum of the MoSe2/hBN/WSe2 device using transfer-matrix calculations. Starting with the dimensions estimated from AFM measurements of graphite and hBN flakes (Table S1), we varied the dielectric constants of MoSe2 and WSe2 layers with parameters such as the oscillator strength, peak energy, and linewidth, until the calculated reflection contrast spectrum match the experimental one. From the fit (orange line in Fig. 1e), the central energies and linewidths of A exciton peaks are determined as $E_{MoSe_2} = 1.6217$ eV, $\Gamma_{MoSe_2} = 12.0$ meV, $E_{WSe_2} = 1.6923$ eV, and $\Gamma_{WSe_2} = 13.8$ meV.
<table>
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<th>Structure</th>
<th>Thickness</th>
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<td>Top hBN</td>
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<td>Top graphite</td>
<td>5 nm</td>
</tr>
<tr>
<td>Middle hBN</td>
<td>30 nm</td>
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<tr>
<td>MoSe₂ (1L)</td>
<td>0.64 nm</td>
</tr>
<tr>
<td>Spacer hBN (3L)</td>
<td>1.0 nm</td>
</tr>
<tr>
<td>WSe₂ (1L)</td>
<td>0.65 nm</td>
</tr>
<tr>
<td>Bottom hBN</td>
<td>80 nm</td>
</tr>
<tr>
<td>Bottom graphite</td>
<td>5 nm</td>
</tr>
<tr>
<td>SiO₂</td>
<td>285 nm</td>
</tr>
<tr>
<td>Si substrate</td>
<td>525 μm</td>
</tr>
</tbody>
</table>

Table S1 | Estimated structural dimensions for the device used in the main text.

An absorption coefficient $\alpha$ is defined as the fraction of the power absorbed in a unit length of the medium. If the beam is propagating in the $z$ direction and the incident intensity is $I_0$, then Beer’s law states that the intensity at position $z$ is

$$I(z) = I_0 e^{-\alpha z}.$$ (S2)

Considering the complex refractive index $\tilde{n} = n + i\kappa$, the electric-field propagation is described as

$$\mathcal{E}(z, t) = \mathcal{E}_0 e^{i(kz - \omega t)} = \mathcal{E}_0 e^{i(\tilde{n}\omega z/c - \omega t)} = \mathcal{E}_0 e^{i(n\omega z/c - \omega t)} e^{-\kappa \omega z/c}.$$ (S3)

By comparing the exponential decay constants in Eqs. (S2) and (S3), considering that the optical intensity is $I \propto \mathcal{E}\mathcal{E}^*$, the absorption coefficient can be derived as $\alpha = 2\kappa \omega / c$. Therefore, the imaginary refractive index $\kappa$ is directly related to the absorption coefficient $\alpha$. By modeling complex dielectric constants $\tilde{\varepsilon} = \varepsilon_1 + i\varepsilon_2$ with Lorentzian oscillators and fitting them to an experimental reflection contrast spectrum, we can estimate the values of imaginary refractive index

$$\kappa = \sqrt{\frac{-\varepsilon_1 + \sqrt{\varepsilon_1^2 + \varepsilon_2^2}}{2}}$$ (S4)

and, subsequently, the absorption coefficient $\alpha = 2\kappa \omega / c$. The total amount of absorption by a monolayer with thickness $d$ at an angular frequency $\omega$ is then estimated as

$$A(\omega) = \frac{I_0 - I(d)}{I_0} = 1 - e^{-\alpha d} = 1 - e^{-2\kappa \omega d/c}.$$ (S5)
Alternatively, we can simply perform a transfer-matrix calculation to estimate the power reflectance $\mathcal{R}$ and power transmittance $\mathcal{T}$ of the sample (“sb”) and background (“b”) regions using the extracted complex dielectric constants (from the fit to the measured reflection contrast spectrum), and then calculate the absorption in each region as $A_{\text{sb}} = 1 - \mathcal{R}_{\text{sb}} - \mathcal{T}_{\text{sb}}$ and $A_{\text{b}} = 1 - \mathcal{R}_{\text{b}} - \mathcal{T}_{\text{b}}$. The monolayer absorption is then calculated as $A = A_{\text{sb}} - A_{\text{b}}$. We find that both methods yield similar values of monolayer absorption $A(\omega)$.

Due to the sharp spectral features of both the pump and sample, estimation of the pump absorption has an additional complication. To take the spectral mismatch into account, we integrated the pump spectrum $I_{\text{pump}}(E)$ multiplied by the fitted absorption profile $A(E)$ of the MoSe$_2$ exciton peak, and normalized it with the integrated pump spectrum to get the total absorption $A_{\text{tot}}$, which was

$$A_{\text{tot}} = \frac{\int I_{\text{pump}}(E) A(E) \, dE}{\int I_{\text{pump}}(E) \, dE} = 0.0196$$

(S6)

for the pump spectrum $I_{\text{pump}}(E)$ shown in Fig. 1e and sample absorption spectrum $A(E)$ extracted from the transfer-matrix calculation. Note that the value of $A_{\text{tot}}$ varies not only by the mismatch between pump spectrum and sample resonance but also by the vertical stacking structure and its dielectric constants, which affect the strength of the local field at the TMD layer. The measured pump fluence $F_{\text{pump}}$ was converted to the incident photon density $n_{\text{pump}}$, and then converted to the pump-induced MoSe$_2$ exciton density $n_m = A_{\text{tot}} n_{\text{pump}}$. Even if we use a saturable absorber model to estimate the density,

$$n_m = \frac{n_{\text{pump}}}{n_{\text{pump}} + \frac{n_{\text{Mott}}}{A_{\text{tot}}}} \cdot n_{\text{Mott}}$$

(S7)

where $n_{\text{Mott}}$ is the excitonic Mott density, the density-dependent trends shown in Fig. 5 do not change significantly.
**Figure S5 | Estimation of pump absorption $A_{tot}$**. Extracted sample absorption (from the reflection contrast spectrum fit in Fig. 1e) is plotted in blue (left axis). Pump spectra in the background region ($I_{\text{pump}}^b$, light gray) and the sample region ($I_{\text{pump}}^s$, dark gray) are plotted (right axis).

The transferred hole density $n_w$ in the WSe$_2$ layer can be estimated from the saturation of the exciton absorption peak at $E_x$ or from the appearance of the trion absorption peak at $E_t$. We measured a gate-dependent reflection contrast spectrum at 4 K (Fig. S6a), which shows well-defined exciton and trion features on both the WSe$_2$ hole-doped side and the MoSe$_2$ electron-doped side. Line cuts at various back-gate voltages ($V_{bg}$) are shown in Fig. S6b and line cuts at $E_x$ and $E_t$ are shown in Fig. S6c. The WSe$_2$ hole density $n_w$ (the x axis of Fig. S6c) is calibrated using a capacitor model with $\epsilon_{\text{hBN}} = 4.2$ and $d_{\text{hhBN}} = 80$ nm (measured by an AFM). In the regime we are concerned with, the absorption change is linear with $n_w$ (fit to linear dependences are shown with block dotted lines in Fig. S6c). This way, the saturation of the exciton peak (or appearance of the trion peak) can be correlated with $n_w$. The linear fit is valid for the results shown in Figs. 2-5, where the transferred hole density is well below the Mott density (the change of WSe$_2$ exciton absorption induced by the pump is up to $|\Delta A/A|_{\text{max}} \sim 12\%$).

We also show a simulated pump-probe spectrum in Fig. S6d using the gate-dependent reflection spectrum. A pump-off spectrum $R_{\text{pump off}}$ is simulated by the reflection spectrum at the charge-neutral point (~0.5 V) and a pump-on spectrum $R_{\text{pump on}}$ is simulated by the reflection spectra at various gate voltages from −1 V to −3 V. The resulting pump-probe spectra, $\Delta R/R = (R_{\text{pump on}} - R_{\text{pump off}})/R_{\text{pump off}}$, show the saturation of the exciton peak ($\Delta R/R > 0$ at $E_x$) and the appearance of the trion peak ($\Delta R/R < 0$ at $E_t$), similar to the measured pump-probe spectra.
shown in Fig. 3c,d.

**Figure S6 | Estimation of transferred hole density in WSe₂.** a, Gate-dependent reflection contrast spectrum at 4 K. b, Line cuts of a near the WSe₂ exciton energy at six different back-gate voltages (Vbg). c, Reflection contrast at the WSe₂ exciton energy (green, 1.7195 eV) and at the WSe₂ trion energy (orange, 1.6989 eV). Shaded areas shown in b denote where the average values were taken. Black dotted lines are fit results to a linear dependence. d, Pump-probe spectra simulated using reflection spectra at different gate voltages. The reflection spectrum at –0.5 V is taken as a pump-off spectrum (R_{pump off}), and the reflection spectra at various Vbg’s are taken as pump-on spectra (R_{pump on}). Simulated pump-probe spectra can be calculated by \( \Delta R/R = (R_{pump on} - R_{pump off})/R_{pump off} \), which show a negative dip at the WSe₂ trion energy and a positive peak at the WSe₂ exciton energy.
5. Results of coupled rate equations fitting

In Fig. S7, we provide a few different fitting results of Eqs. (1) and (2) when different starting parameters and bounds are used. In particular, the goodness of fit and the fitted charge transfer time $\tau_t = 1/\gamma_t$ were dependent on the starting value of the MoSe$_2$ exciton lifetime $\tau_m = 1/\gamma_m$.

For the results shown in Fig. S7a-c, which is identical to that shown in Fig. 5, the starting value of $\tau_m$ was set to 100 ps but was allowed to be varied up to 30% at different excitation densities. The density-dependent exciton lifetime accounts for nonlinear processes that are not fully captured by the exciton-exciton annihilation term $\frac{1}{2} \gamma_{mn} n_m^2$. Other fit parameters are $\gamma_w = (4 \text{ ns})^{-1}$, $\gamma_{mm} = 0.27 \text{ cm}^2/\text{s}$, $\gamma_t = (500 \text{ ps})^{-1}$, and $\alpha = 2.3\%$.

For the results shown in Fig. S7d-f, the starting value of $\tau_m$ was allowed to be varied from 200 ps to 10 ps at different excitation densities. This gave the best fitting across all densities—both the slow rise at the low excitation densities and the fast rise at the high excitation densities are well captured. Other fit parameters are $\gamma_w = (5 \text{ ns})^{-1}$, $\gamma_{mm} = 0.23 \text{ cm}^2/\text{s}$, $\gamma_t = (500 \text{ ps})^{-1}$, and $\alpha = 2.9\%$. However, such a wide range of $\tau_m$ values may not be physical.

For the results shown in Fig. S7g-i, the final value of $\tau_m$ was fixed for all excitation densities. When the starting value of $\tau_m$ was 100 ps, the final value of $\tau_m = 61 \text{ ps}$ gave the best fit to all curves. The resulting parameters are $\gamma_w = (4 \text{ ns})^{-1}$, $\gamma_{mm} = 0.47 \text{ cm}^2/\text{s}$, $\gamma_t = (190 \text{ ps})^{-1}$, and $\alpha = 1.6\%$. However, the fits at both the low and high excitation densities are poor, not being able to reproduce the slow rise at the low excitation densities and fast rise at the high excitation densities.

For the results shown in Fig. S7j-l, the final value of $\tau_m$ was fixed for all excitation densities. When the starting value of $\tau_m$ was 200 ps, the final value of $\tau_m = 175 \text{ ps}$ gave the best fit to all curves. The resulting parameters are $\gamma_w = (3 \text{ ns})^{-1}$, $\gamma_{mm} = 0.34 \text{ cm}^2/\text{s}$, $\gamma_t = (500 \text{ ps})^{-1}$, and $\alpha = 2.3\%$. The fits are better than Fig. S7g-i at the low excitation densities, but not as good as Fig. S7a-f.

From different starting parameters, we consistently observed that the charge transfer rate is $\gamma_t \sim (500 \text{ ps})^{-1}$. Our estimate is consistent with the measured transfer efficiencies and the effective decay rate of MoSe$_2$ excitons at 100 K.
Figure S7 | Results of the coupled rate equations fitting with different conditions.
6. Momentum mismatch between MoSe$_2$ and WSe$_2$ valleys

Interlayer excitons are not only separated in real space, but also in momentum space depending on the twist angle and lattice mismatch between the two layers, which further modifies recombination pathways and dynamics$^9$. Using the lattice constants of MoSe$_2$ and WSe$_2$ layers, $a_m = 3.29$ Å and $a_w = 3.28$ Å, their momenta at K valleys from the Γ point can be calculated as $k_{m,K} = 4\pi/3a_m = 1.273$ Å$^{-1}$ and $k_{w,K} = 4\pi/3a_w = 1.277$ Å$^{-1}$. The distance between the two points in the momentum space is given by

$$\Delta k = \sqrt{k_{m,K}^2 + k_{w,K}^2 - 2k_{m,K}k_{w,K}\cos \theta_{\text{twist}}},$$

where $\theta_{\text{twist}} = 19.5^\circ$ for the device used in the main text. The momentum mismatch between the K valleys of MoSe$_2$ and WSe$_2$ is $\Delta k = 0.43$ Å$^{-1}$, while the momentum mismatch between the MoSe$_2$ K valley and WSe$_2$ K$'$ valley is $0.88$ Å$^{-1}$. We performed a circular dichroism measurement where the pump beam was right-circularly polarized ($\sigma^+$) and the pump-probe spectra with right- and left-circular ($\sigma^+$ and $\sigma^-$) probe beams are compared, which shows that the transfer timescale and efficiencies from K$_{\text{MoSe}_2}$ to K$_{\text{WSe}_2}$ valleys are similar to that from K$_{\text{MoSe}_2}$ to K$'$$_{\text{WSe}_2}$ valleys (within 10%).

The measurement of twist-angle-dependent charge transfer dynamics can potentially identify which momentum pathway it takes (either direct transfer from MoSe$_2$ K valley to WSe$_2$ K valley or via Q valley that has a mixed character), while the temperature dependence can give information about the population of phonons that connect the momentum and energy mismatch. Previous twist-angle-dependent or temperature-dependent measurements were not able to find any significant variations greater than the instrumental time resolution (10-100 fs). Overcoming the instrument response limit would allow us to accurately compare the transfer timescales under different conditions. Using extremely short pulses (<10 fs), however, is not only technically challenging, but also not ideal in a sense that the material response cannot keep up with the extremely short perturbation (in other words, the system does not interact strongly with the nonresonant part of the ultrashort broadband pump). Therefore, the slow charge transfer in TMD/hBN/TMD offers new possibilities to investigate the charge transfer mechanism.